

# **Molecular dynamics simulation of localized electrochemical deposition**

**LAMMPS Workshop and Symposium  
August 12, 2021**

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**University of Cincinnati  
Micro and Nano Manufacturing Laboratory**

<https://ceas.uc.edu/research/centers-labs/micro-and-nano-manufacturing-laboratory.html>

# Outline

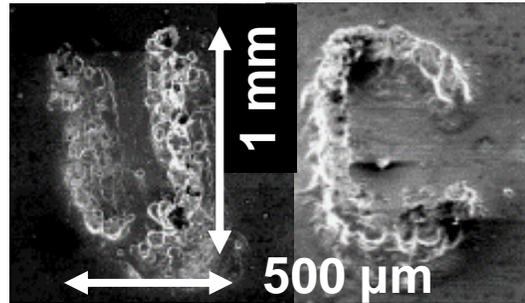
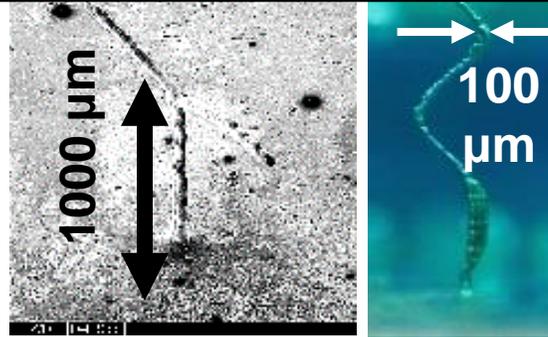


- **UC Micro and Nano Manufacturing Laboratory**
- Electrochemical Additive Manufacturing (ECAM)
- Why molecular dynamics?
- System setup and method
- Results and discussion
- Conclusions
- Acknowledgments

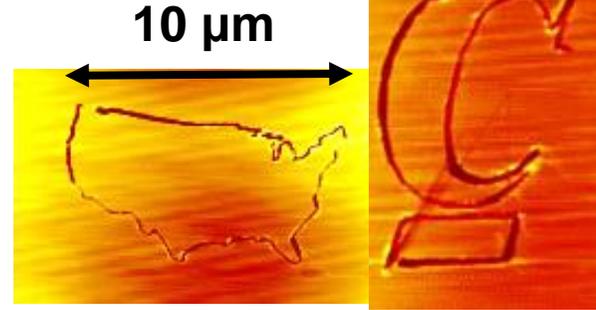
# UC Micro and Nano Manufacturing Laboratory

- Technology grows increasingly smaller, lighter, and more powerful over time
- It has been possible by researching how to harness scientific principles to add or remove material at the small scale
- Our lab, the **Micro and Nano Manufacturing Laboratory**, performs this type of research to make a wide variety of micro and nano manufacturing processes possible, as seen in the images to the right

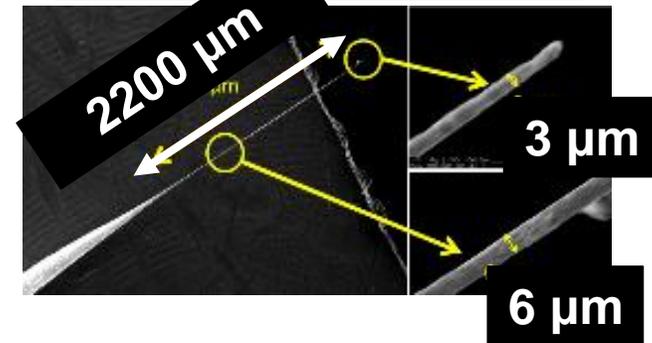
**3D printing small shapes**



**Engraving small shapes**



**Etching small tools**

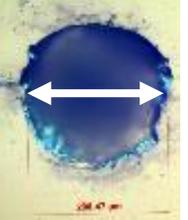


**Drilling small holes**

**180 μm**



**200 μm**



The long-term intention is for these technologies to eventually be commercially adopted.

# Outline

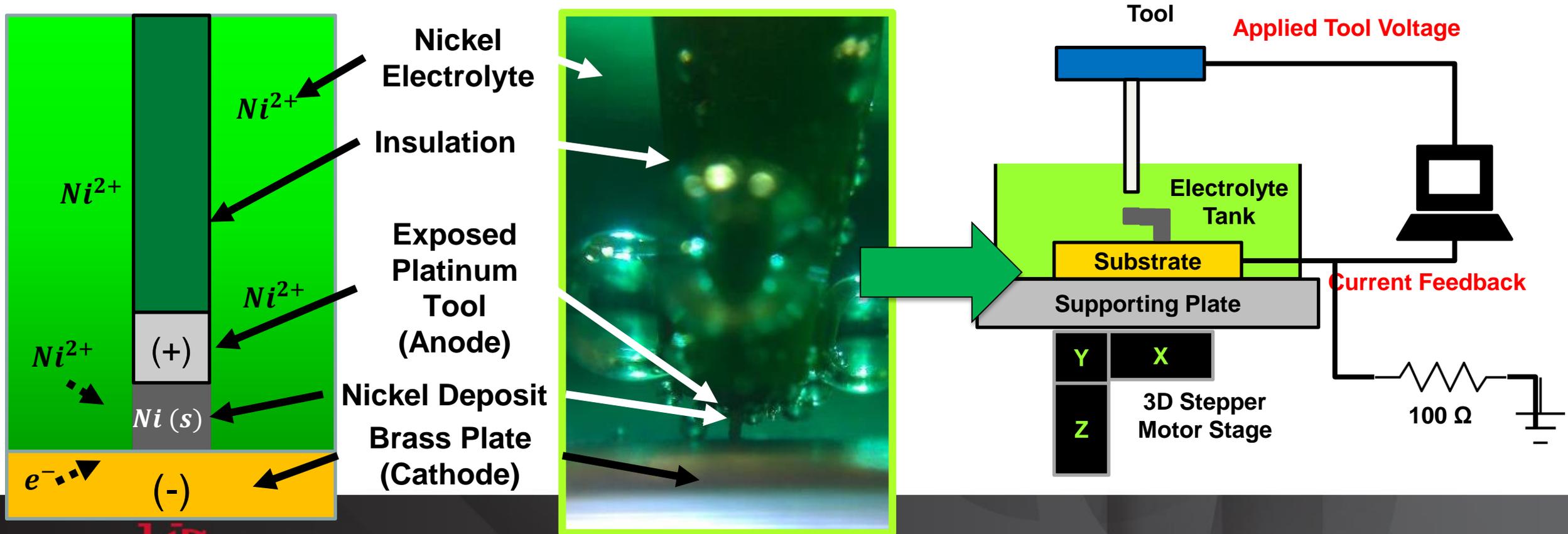


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# Electrochemical additive manufacturing

## Introduction and working principle

- A nontraditional method of additive manufacturing
- Performed using localized metal deposition with 3-axis positioning and control



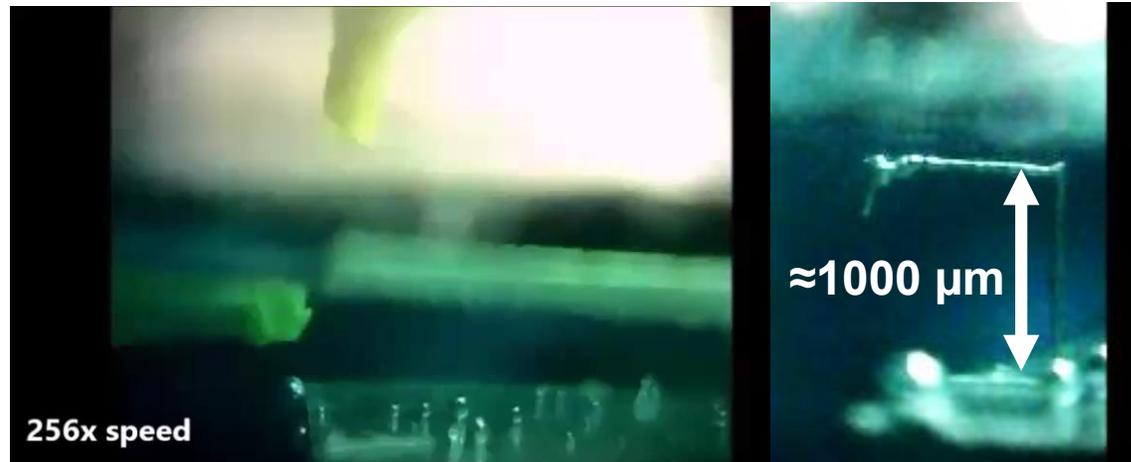
# Electrochemical additive manufacturing

## Video Demonstration: Overhanging Structure

- <https://www.youtube.com/watch?v=0efMAGZI9XI>
- This video shows the voxel-by-voxel nature of material addition by metal plating, which allows for support structures to be avoided

Video of Deposition

Resulting Shape



## Advantages over conventional additive manufacturing methods

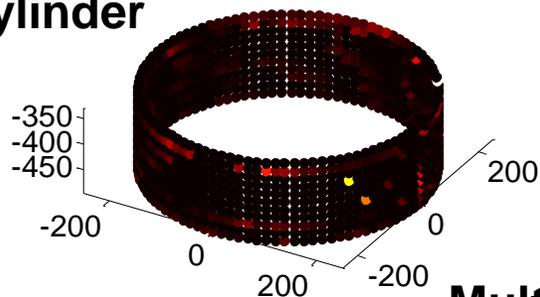
	MJ	ME	SLA	SLS	ECAM
Can deposit metal parts?	☹️	☹️	☹️	😊	😊
Avoids support structures?	☹️	☹️	☹️	☹️	😊
Avoids residual stress/thermal defects?	☹️	☹️	☹️	☹️	😊
Avoids post-processing steps?	☹️	☹️	☹️	☹️	😊
Can achieve < 1 μm resolution?	☹️	☹️	☹️	☹️	😊

# Electrochemical additive manufacturing

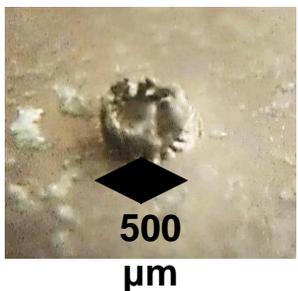
## Experimental proof-of-concept

- A variety of CAD geometries can be created by ECAM, including support structure-less overhangs

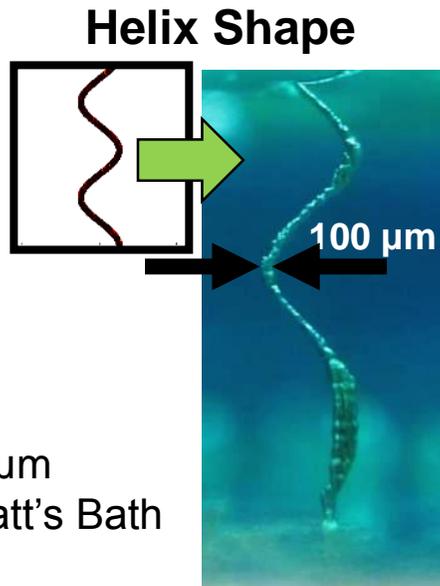
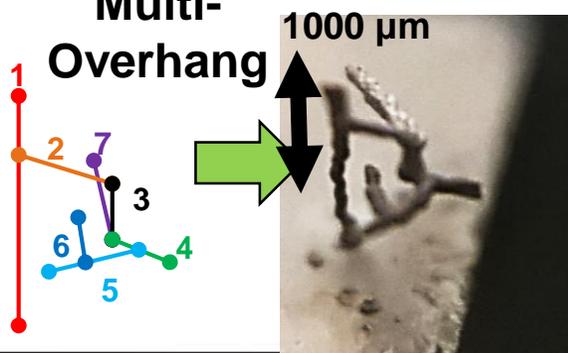
### Cylinder



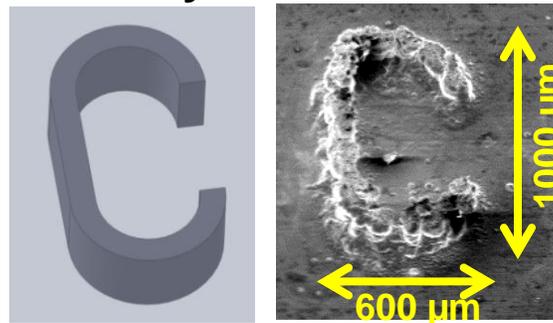
Tool size: 250  $\mu\text{m}$   
 Electrolyte: Watt's Bath  
 Voltage: 5 V



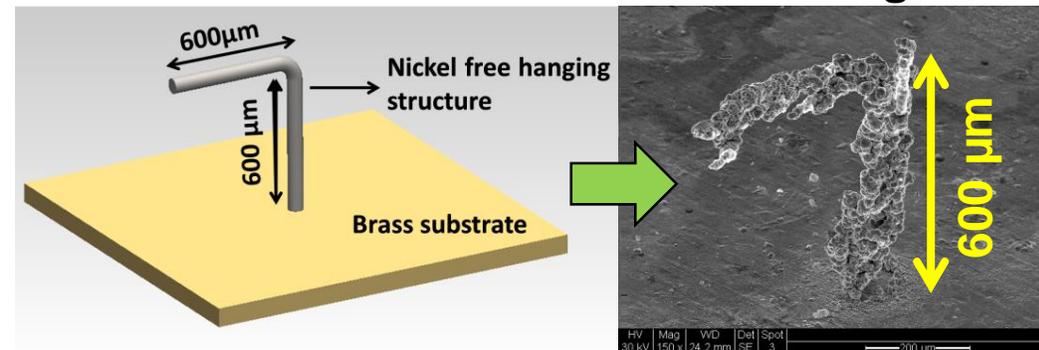
### Multi-Overhang



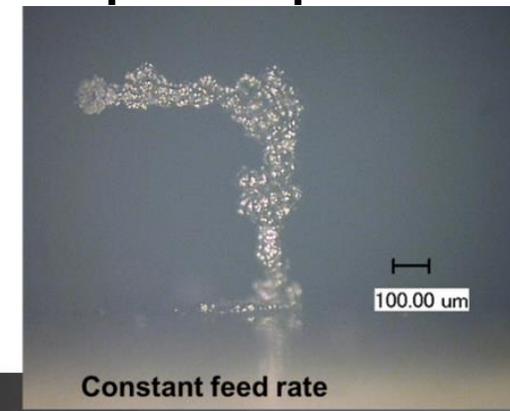
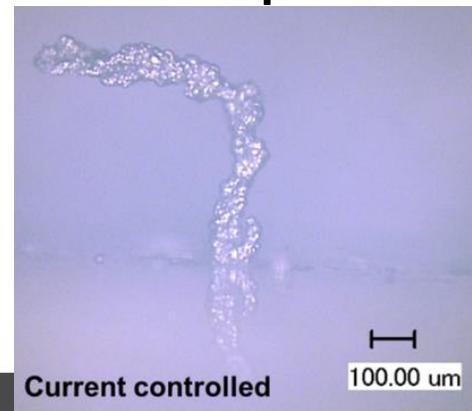
### 30-Layer Part



### Overhang



### Closed-Loop Control vs. Open Loop Control



Brant, Anne. *An Explorative Study of Electrochemical Additive Manufacturing*. MS Thesis. University of Cincinnati, 2016.

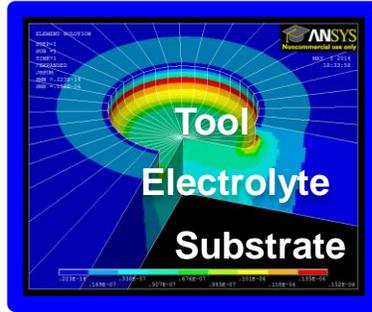
Sundaram, M., Kamaraj, A. B., and Kumar, V. S. (2015). Mask-less electrochemical additive manufacturing: a feasibility study. *Journal of Manufacturing Science and Engineering*, 137(2), 021006.

# Electrochemical additive manufacturing

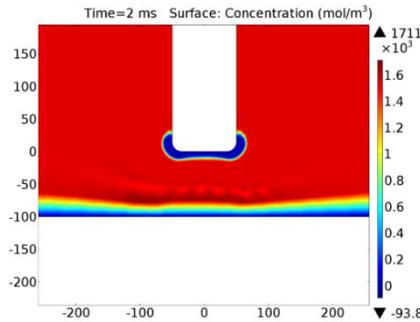
## FEM simulations



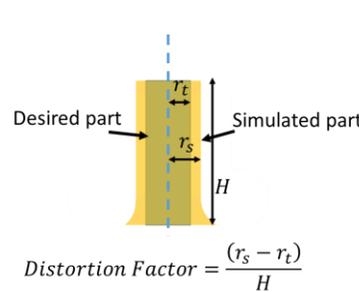
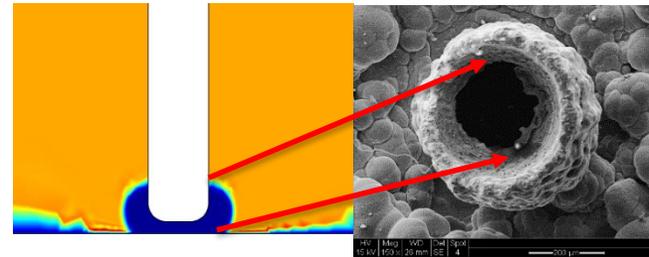
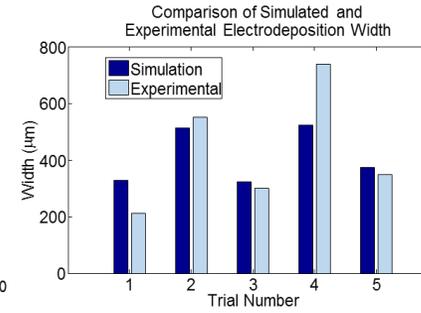
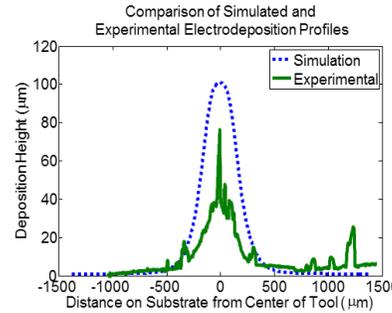
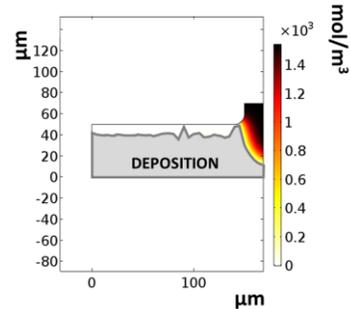
### Thermoelectric Simulation With Moving Boundary



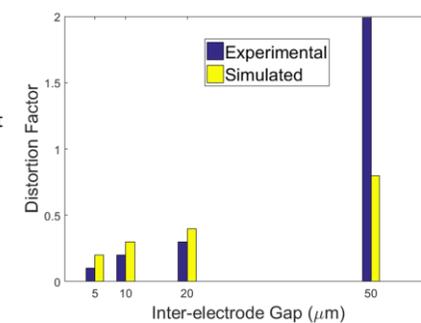
### Concentration Change (Fick's Law) Simulation



### Concentration Change With Moving Boundary



$$\text{Distortion Factor} = \frac{(r_s - r_t)}{H}$$



- Able to approximate deposition profile in response to varying input process parameters
- Able to predict experimental ion depletion behavior at varying IEGs using the simulated concentration profile
- Able to predict and minimize part distortion using results from changing process parameters in the simulation

# Outline

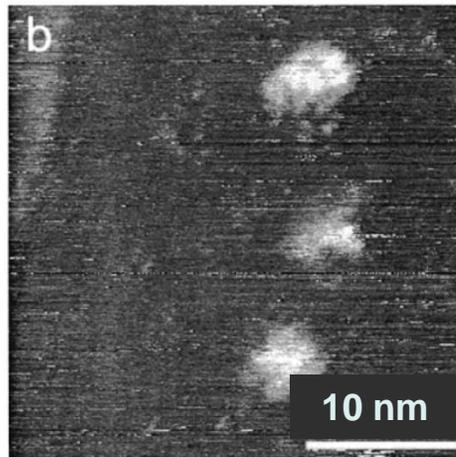
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# Why molecular dynamics?

ECAM is relatively unexplored at the nano scale

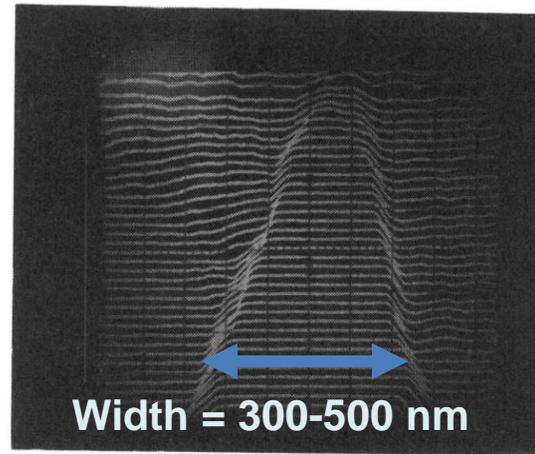
Some work exists in using SPM probes (STM and AFM) to perform localized deposition

**Cu Clusters on Au**



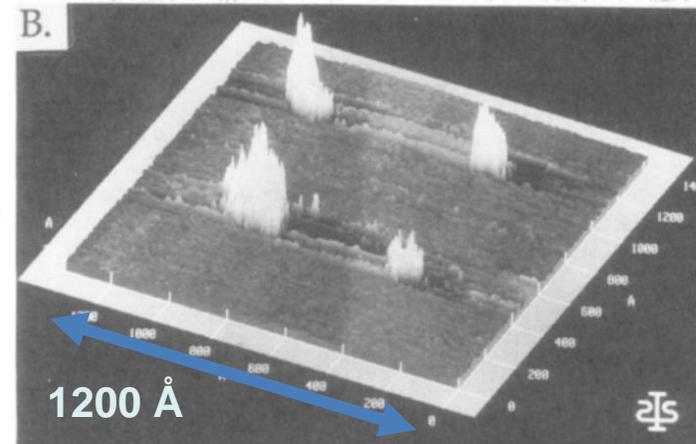
Kirchner, Viola, Xinghua Xia, and Rolf Schuster. "Electrochemical nanostructuring with ultrashort voltage pulses." *Accounts of Chemical Research* 34.5 (2001): 371-377.

**Au Line on Au**



Schneir, J., et al. "Creating and observing surface features with a scanning tunneling microscope." 1988 *Los Angeles Symposium--OE/LASE'88*. International Society for Optics and Photonics, 1988.

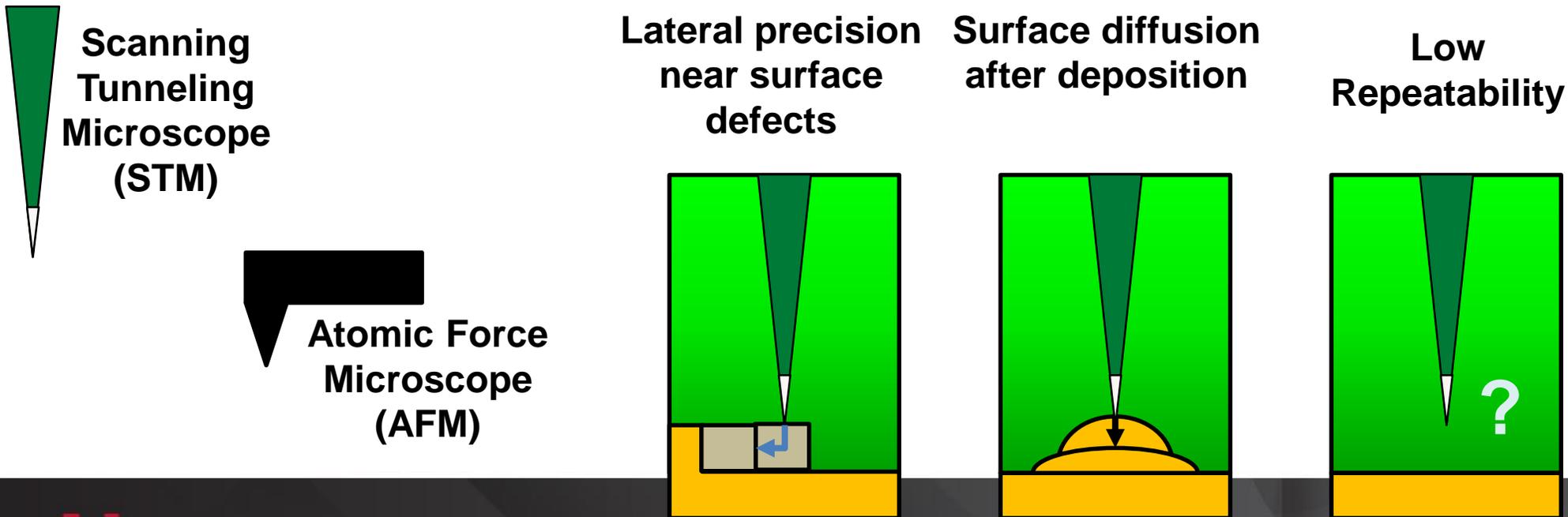
**Cu and Ag Pillars on Graphite**



Li, Wenjie, Jorma A. Virtanen, and Reginald M. Penner. "A nanometer-scale galvanic cell." *The Journal of Physical Chemistry* 96.16 (1992): 6529-6532.

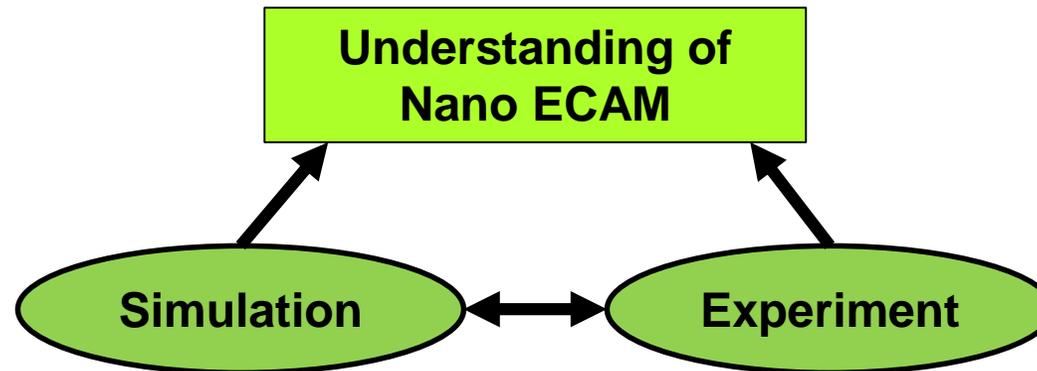
# Why molecular dynamics?

- Existing localized nano deposition work is limited in geometry to lines, pillars, and mounds
- Generally, SPM (scanning probe microscopy) techniques are used
- Challenges in deposition include:



# Why molecular dynamics?

- In order to achieve ECAM at the nano scale, we need:
  - The ability to deposit complex 3D shapes
  - The ability to reliably control where material is deposited and for it to stay in place
- This requires **a clear understanding** of the fundamental process of electrodeposition at the nano scale, achieved using:
  - Experiment
  - Simulation
- Use of molecular dynamics allows for the necessary atomic-scale resolution to model localized deposition at the nano scale



# Outline

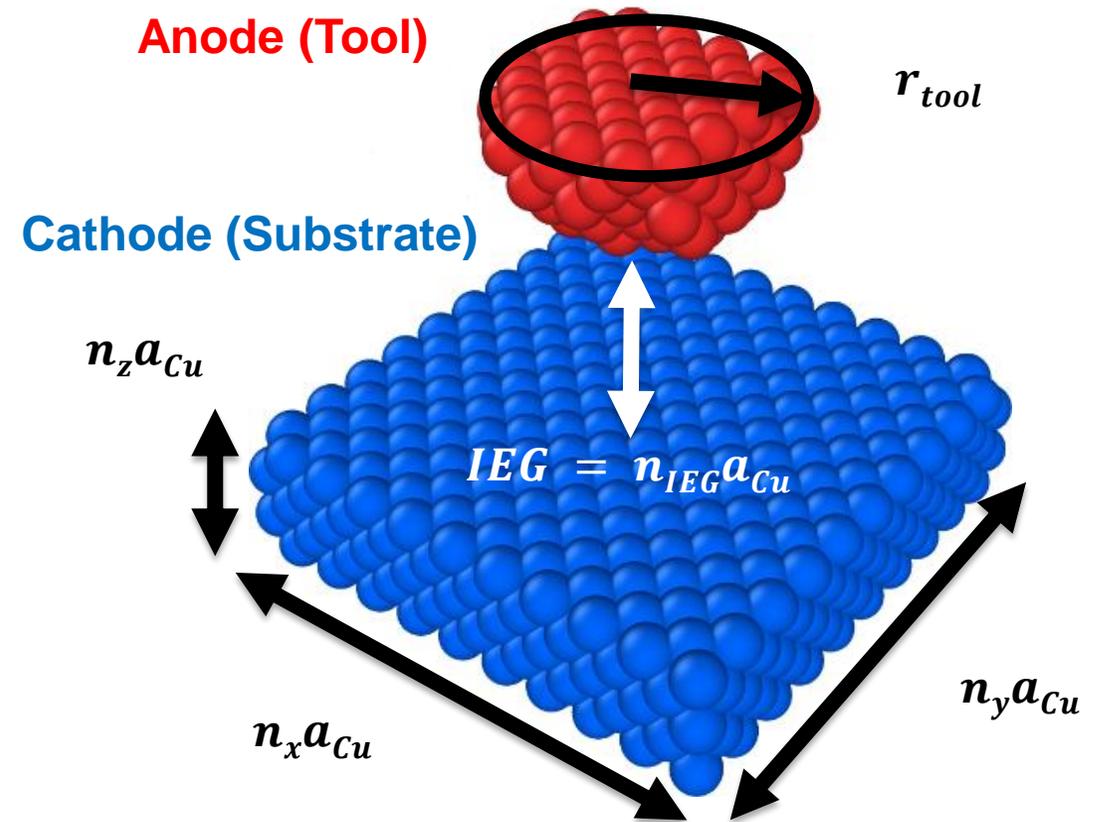


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# System setup and method

## Electrode configuration

- Anodic tool
  - Material: Platinum (Pt)
  - Hemisphere at top of the simulation region
  - Cut from a Pt FCC (100) lattice
  - Adjustable radius
- Cathodic substrate
  - Initially a flat FCC(100) copper slab (later, metal deposit grows on it)
  - Bottom of the simulation space.
- Interelectrode gap (IEG)
  - The space between and surrounding the electrodes where the electrolyte is contained
  - Lateral extent: borders of the cathode (side walls of the simulation region)
  - Vertical extent: cathode surface to the top of the anodic hemisphere (top wall of the simulation region)



# System setup and method

## Electrolyte species

- Explicit cations:  $Cu^{2+}$ 
  - Metal cations, which are actively depositing
- Explicit anions:  $Cl^{-}$ 
  - Act as a counter-charge
  - Some undergo specific adsorption to the substrate
- Solvent: implicit water via Brownian dynamics acting on the ions

## Brownian dynamics equations (applied to each ion):

$$F_{net} = F_{interaction} + F_{frictional} + F_{random}$$

$$F_{frictional} = -\xi_{fric} \mathbf{v} = -6\pi r_i \eta \mathbf{v}$$

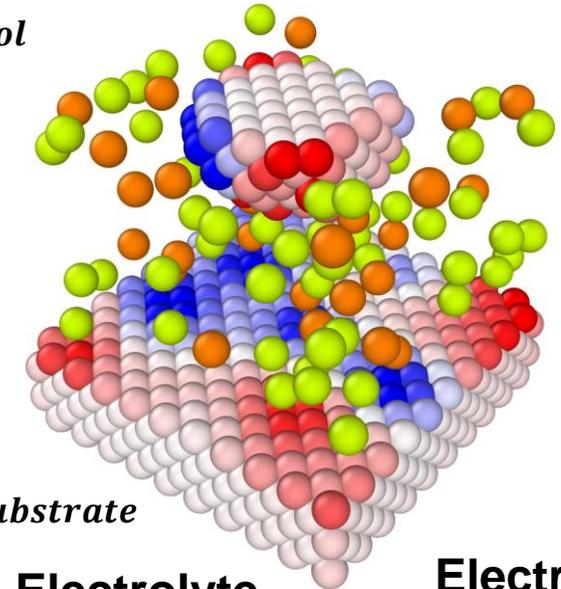
$$F_{random} = [F_{random}^x, F_{random}^y, F_{random}^z]$$

- $F_{net}$  = net applied force
- $F_{interaction}$  = interactions with surrounding ions and metal
- $F_{frictional}$  = frictional force of implicit solvent
- $F_{random}$  = random fluctuations of implicit solvent
- $\mathbf{v}$  = velocity of the ion
- $r_i$  = ionic radius (of  $Cu^{2+}$  or  $Cl^{-}$ )
- $\eta$  = dynamic viscosity of implicit water solvent

Leach, Andrew R., and A. R. Leach. Molecular modelling: principles and applications. Pearson education, 2001.

$V_{tool}$

$V_{substrate}$



## Electrolyte

- $Cu^{2+}$  Cation
- $Cl^{-}$  Anion

## Electrodes

- $q \geq .1$
- $q = 0$
- $q \leq -.1$

# System setup and method

## Interatomic potentials

- Ion-ion and ion-electrode interactions
  - Coulomb interaction
  - Repulsive Lennard-Jones

$$U = \begin{cases} 4\varepsilon \left( \left( \frac{\sigma}{r} \right)^{12} - \left( \frac{\sigma}{r} \right)^6 \right) + \varepsilon & \text{if } r \leq 2\frac{1}{6}\sigma \\ 0 & \text{if } r > 2\frac{1}{6}\sigma \end{cases}$$

- Mixing rules:
  - $\sigma_{ij} = \sigma_{ii}\sigma_{jj}/2$  and  $\varepsilon_{ij} = \sqrt{\varepsilon_{ii}\varepsilon_{jj}}$
- Copper substrate
  - Applied to copper substrate slab
  - The bottom layer of the slab was kept fixed for stability
  - Assumed to be not influenced by LJ or Coulomb interactions from the electrolyte
- Platinum tool
  - Inert: no Pt-Pt interaction + all atoms kept fixed

## Potential Parameters

Ion	$\sigma$ (Å)	$\varepsilon$ (kcal/mol)	$q$
<b>Pt(s)</b>	2.845	7.80	varies
<b>Cu(s)</b>	2.616	4.72	varies
<b>Cu<sup>2+</sup></b>	2.616	4.72	2
<b>Cl<sup>-</sup></b>	4.40	.1	-1

- Platinum and Copper: Heinz H, Vaia R, Farmer B, Naik R. Accurate simulation of surfaces and interfaces of face-centered cubic metals using 12-6 and 9-6 Lennard-Jones potentials. The Journal of Physical Chemistry C. 2008;112:17281-90.
- Chloride: Chandra A. Dynamical Behavior of Anion-Water and Water-Water Hydrogen Bonds in Aqueous Electrolyte Solutions: A Molecular Dynamics Study. The Journal of Physical Chemistry B. 2003;107:3899-906.
- EAM: Foiles S, Baskes M, Daw MS. Embedded-atom-method functions for the fcc metals Cu, Ag, Au, Ni, Pd, Pt, and their alloys. Physical review B. 1986;33:7983.

# System setup and method

## Electrode potentials

- Electrode voltages are held at constant voltages
- Constant-potential governing equation:

$$V_0 = \frac{q_i(t)}{\sqrt{\pi}\xi} + \sum_a \frac{q_a \operatorname{erf}\left(\frac{|\mathbf{r}_i - \mathbf{r}_a|}{\sqrt{2}\xi}\right)}{|\mathbf{r}_i - \mathbf{r}_a|} + \sum_{j \neq i} \frac{q_j \operatorname{erf}\left(\frac{|\mathbf{r}_i - \mathbf{r}_j|}{\xi}\right)}{|\mathbf{r}_i - \mathbf{r}_j|}$$

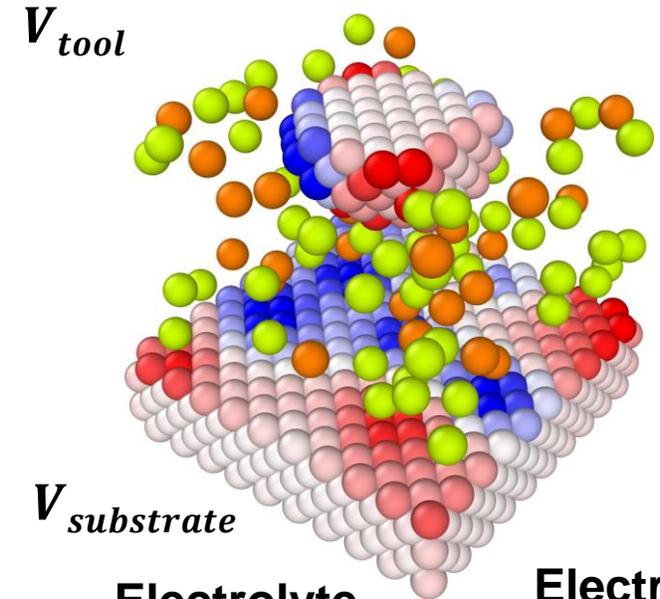
Siepmann, J. Ilya, and Michiel Sprik. "Influence of surface topology and electrostatic potential on water/electrode systems." *The Journal of chemical physics* 102.1 (1995): 511-524.

Where:

$$V_0 = V_{tool} \text{ (for tool atoms)}$$

or

$$V_0 = V_{subs} \text{ (for substrate atoms)}$$



**Electrolyte**

●  $Cu^{2+}$  Cation

●  $Cl^-$  Anion

**Electrodes**

●  $q \geq .1$

○  $q = 0$

●  $q \leq -.1$

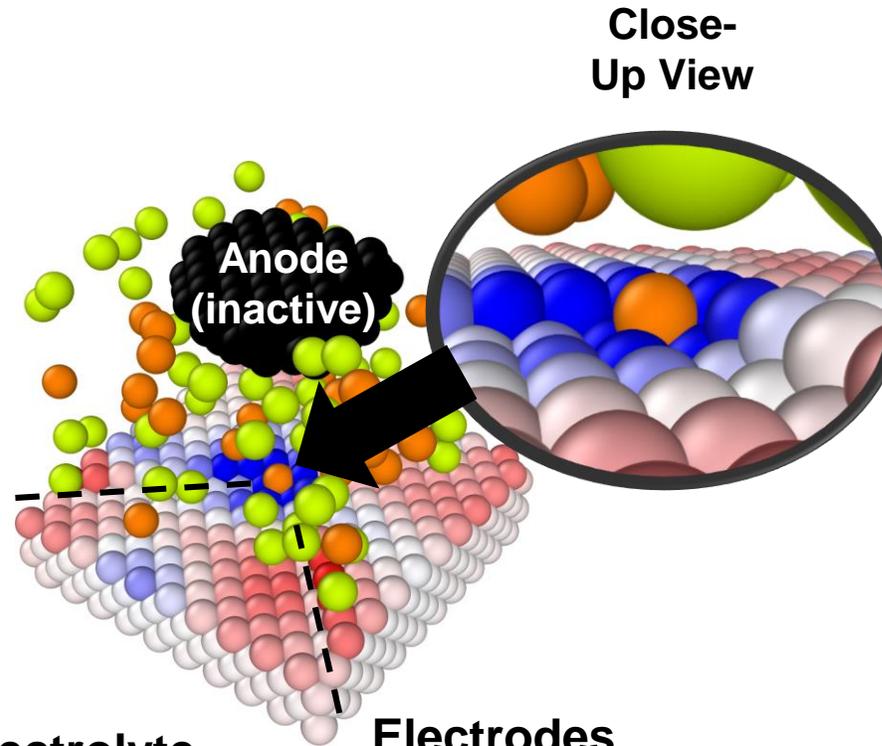
# System setup and method

## Potential reference for deposition

- A special simulation with an inactive tool and a cation in a substrate kink was run to compute a reference values  $\mu_0$  and  $\varphi_0^S$  for cation deposition
- This consisted of the sum of EAM and electrostatic interactions (respectively) for the cation in the reference kink position

### Equilibrium Kink Condition

$$\mu_0 = U_{EAM} \quad \varphi_0^S = \sum_{j \neq i} (kq_j/r_{ij})$$



### Electrolyte

- $Cu^{2+}$  Cation
- $Cl^-$  Anion
- Phantom Ion

### Electrodes

- $q \geq .1$
- $q = 0$
- $q \leq -.1$

## Criterion for deposition reaction

- When the copper ion was near the substrate, two values were computed
- $U_{EAM}$  = EAM potential if ion joins metal lattice in its current position
- $\mu = \mu_0 - ze_0(\varphi_0^S - \varphi^S)$  = potential if ion remains aqueous
- If  $U_{EAM} < \mu$ , then the ion was switched from the aqueous state to the metal state in its current position

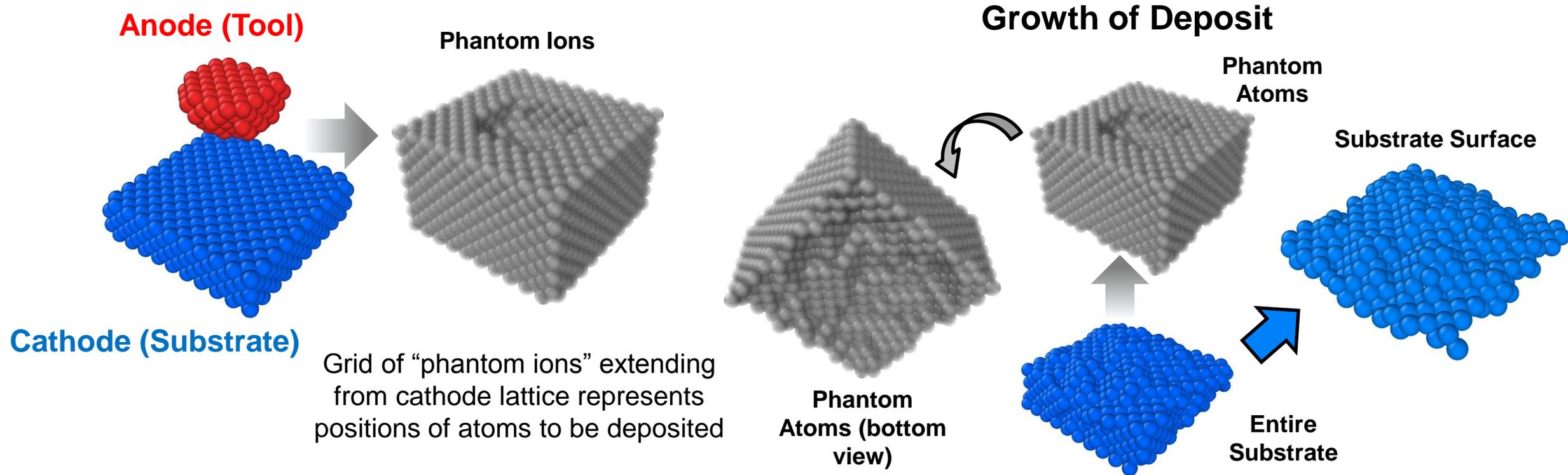
Idea based on:

- Simulation method using EAM vs fixed background potential: Mariscal, M., et al. "The structure of electrodeposits—a computer simulation study." *Applied Physics A* 87.3 (2007): 385-389.
- Role of overpotential in metal deposition: Paunovic, Milan, and Mordechay Schlesinger. *Fundamentals of electrochemical deposition*. Vol. 45. John Wiley & Sons, 2006.

# System setup and method

## Phantom ion matrix

- A background grid of imaginary “phantom ions” (extension of Cu lattice) was used to assist with volume and surface area calculations

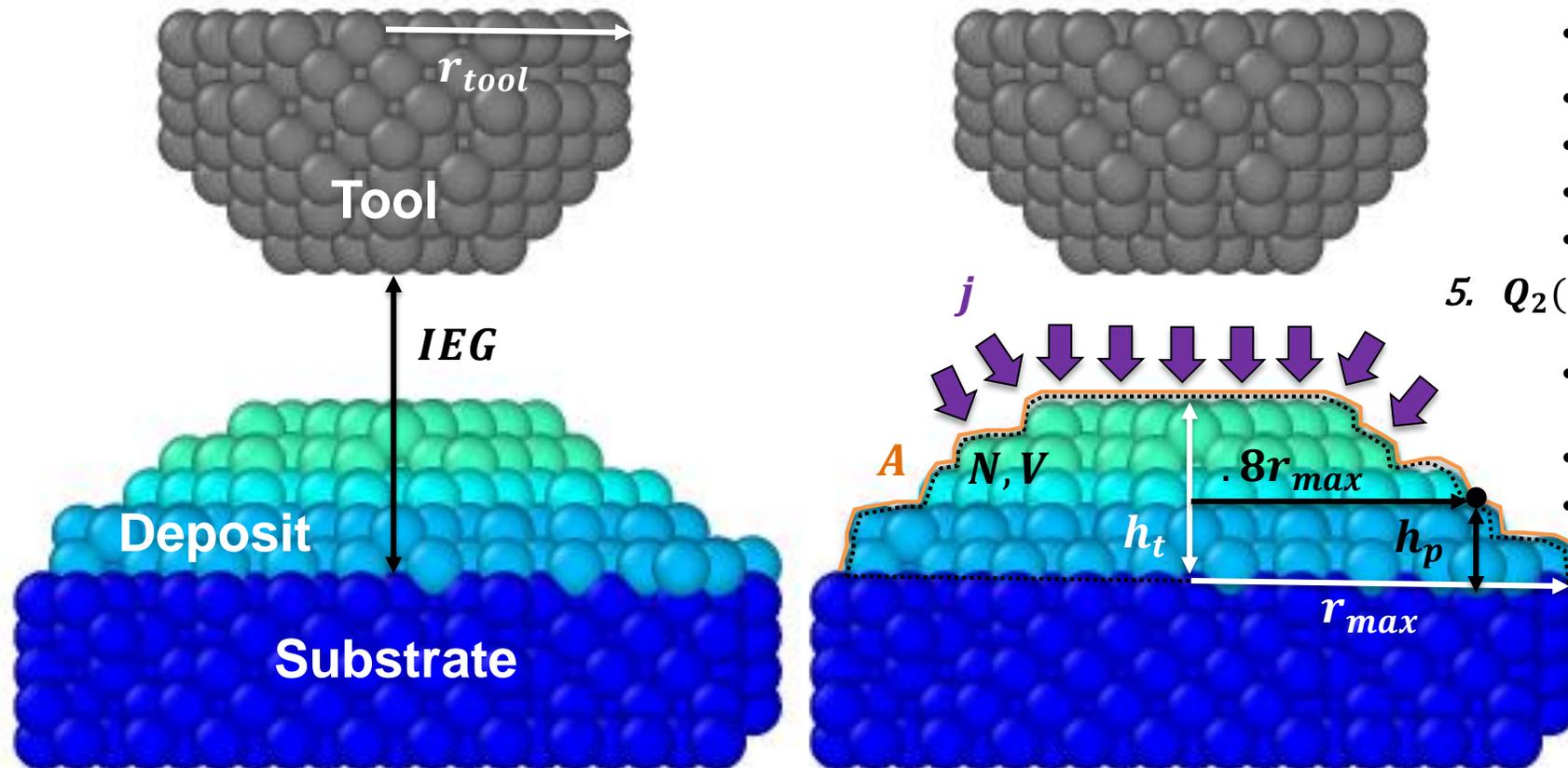


# System setup and method

## Postprocessing – evaluation of the deposition behavior

- Study effect of input geometrical parameters on output deposit behavior

1. Tool radius  $r_{tool}$
2. Interelectrode gap  $IEG$



1.  $h_t(t)$  = Deposit height over time
2.  $N(t)$  = Atoms deposited over time
3.  $j(t)$  = Avg. current density over time
4.  $Q_1(t)$  = Quality factor 1 (height ratio)
  - $Q_1(t) = \frac{h_t - h_p}{h_t}$
  - $h_t$  = total height of deposit
  - $r_{max}$  = max. radius of deposit
  - $.8r_{max}$  = 80% of  $r_{max}$
  - $h_p$  = plating height (height at  $.8r_{max}$ )
5.  $Q_2(t)$  = Quality factor 2 (volume-area ratio)
  - $Q_2(t) = \frac{\frac{V(t)}{A(t)} - \frac{V(0)}{A(0)}}{\frac{V(0)}{A(0)}}$
  - $V(t)$  = volume of deposit
  - $A(t)$  = surface area of deposit

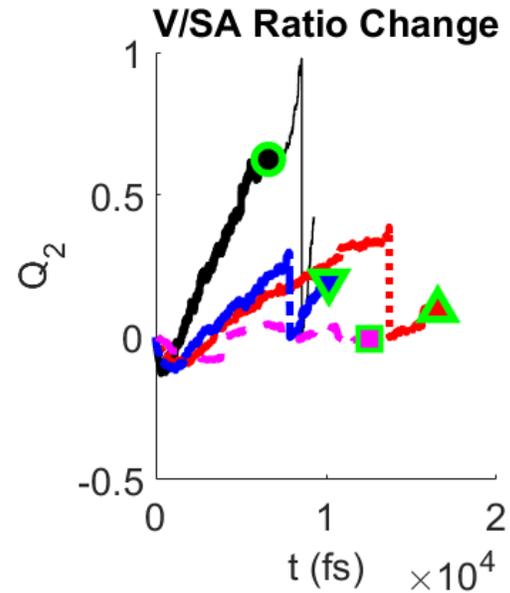
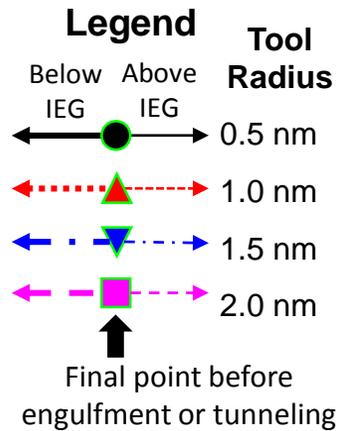
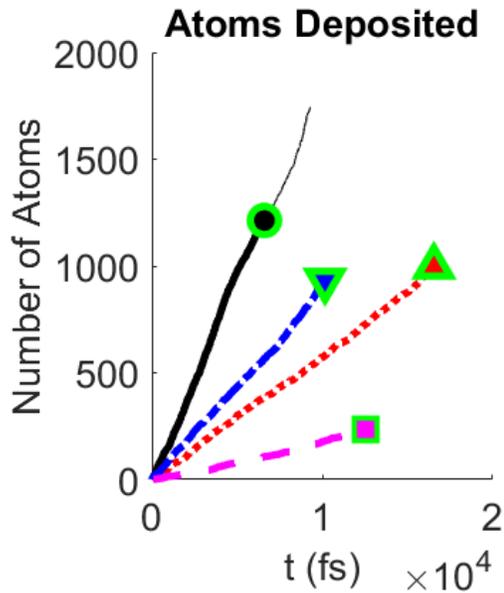
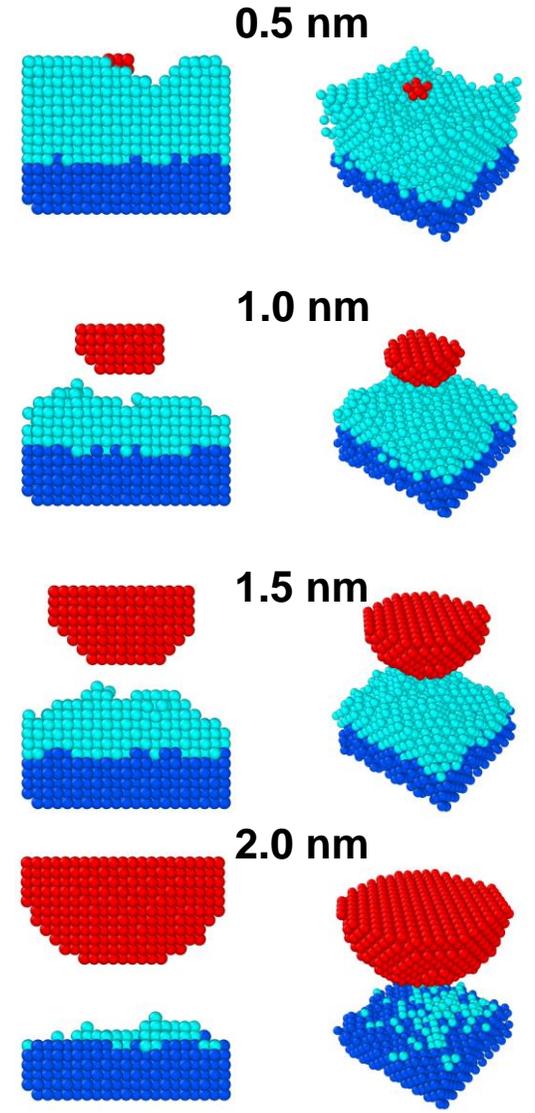
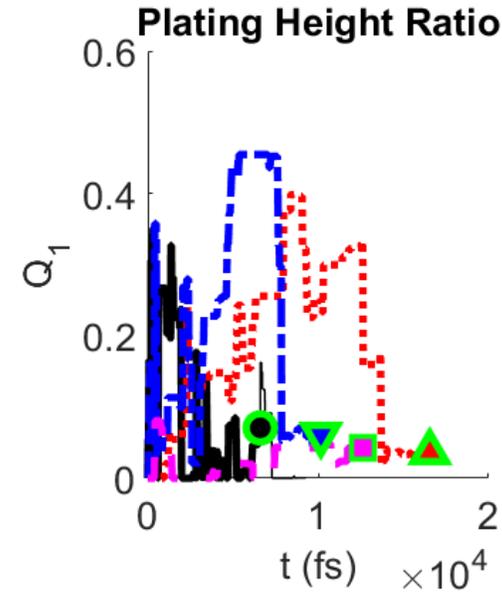
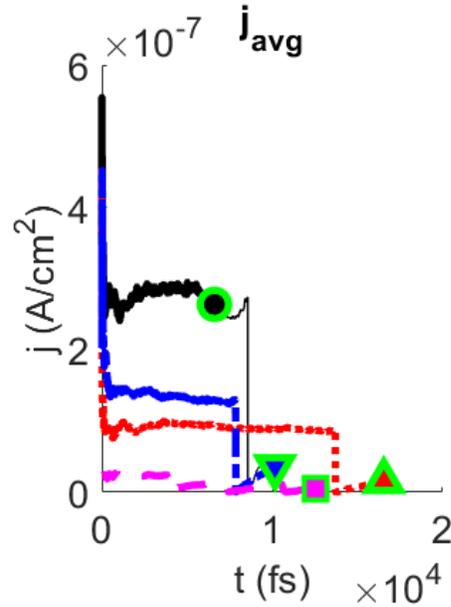
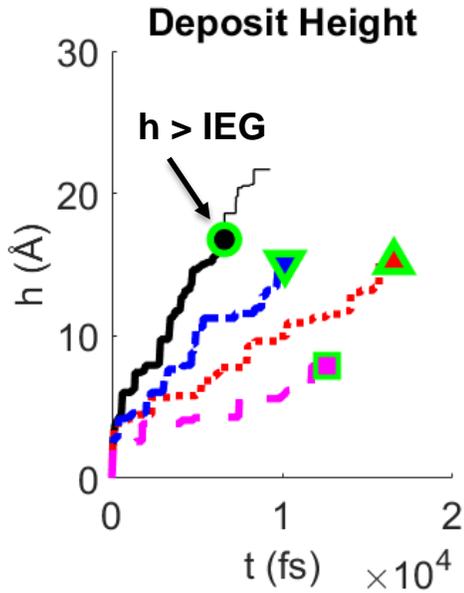
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# Results and Discussion

## Effect of tool radius on the deposition behavior



- Tool
- Cathode (Deposit)
- Cathode (Original)

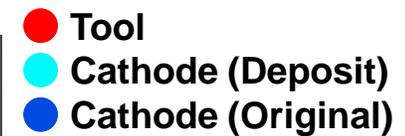
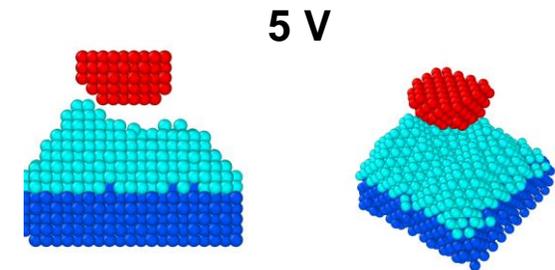
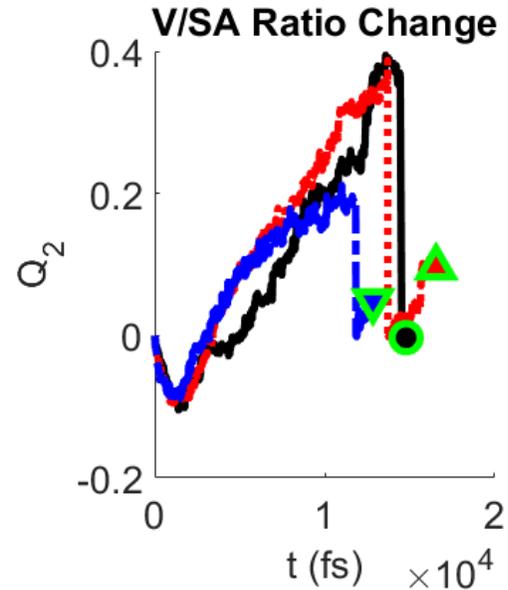
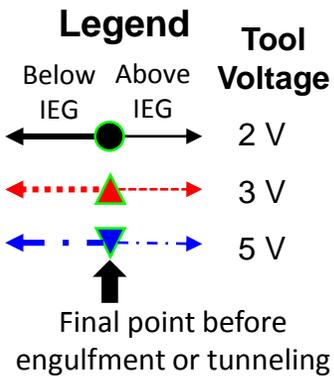
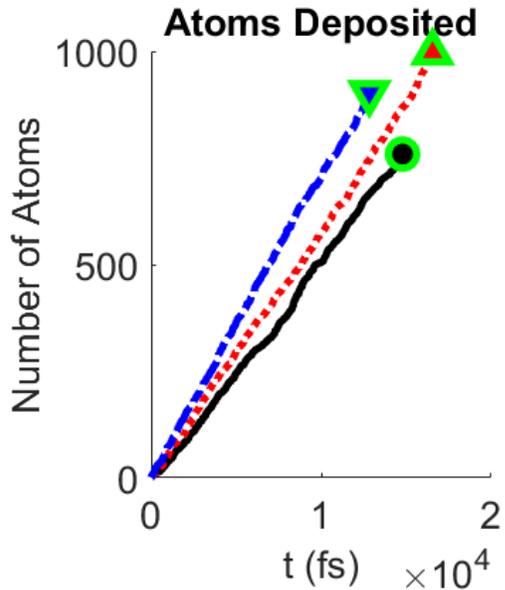
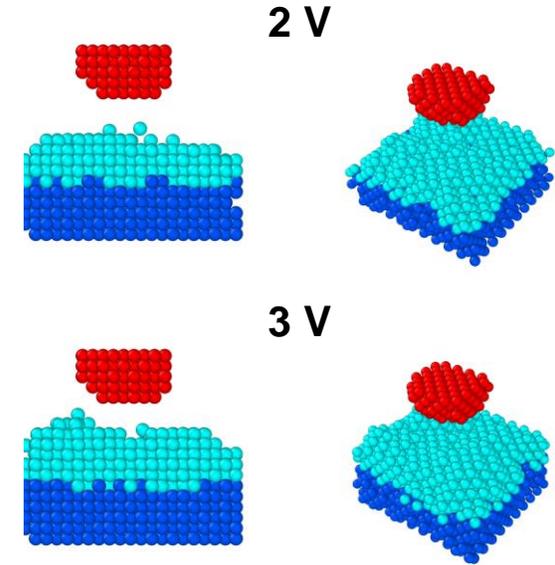
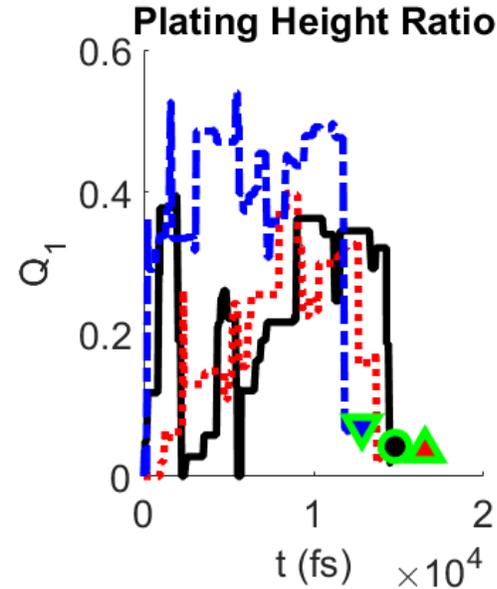
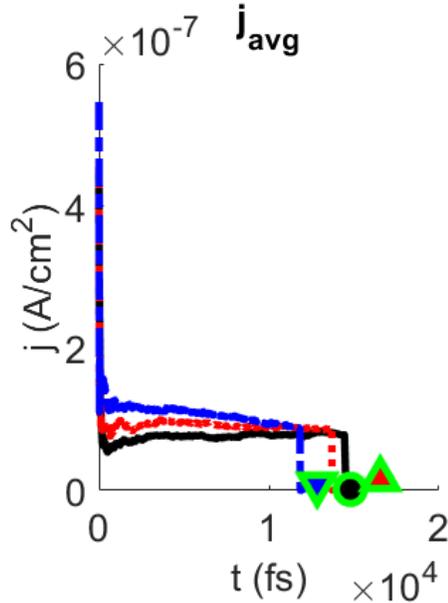
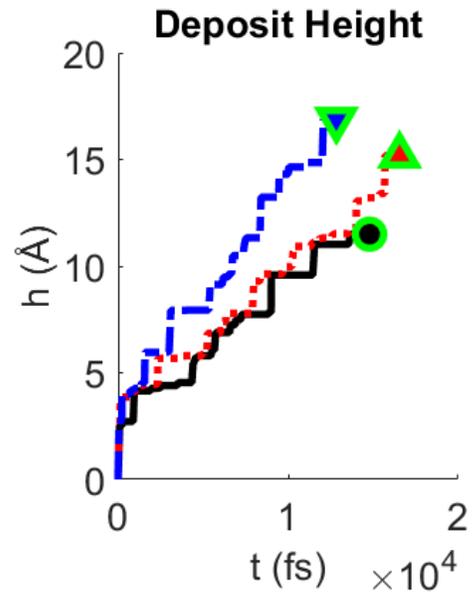
# Results and Discussion

## Effect of tool radius on the deposition behavior

- Effects of increasing the tool radius from intermediate values
  - decrease in deposit quality
  - likely due to distribution of the electric field and sparser charge density distribution
- Effects of reducing the tool radius from intermediate values
  - Also decrease in deposit quality
  - Likely explained by less atoms present to exert an electrostatic force on the cations
  - Even though the smallest tool would have had the strongest induced charges, electric field per atom, and overall current density
- Optimal radius
  - Under these conditions, an optimal radius value of 1.5 Å gives the best quality of deposition

# Results and Discussion

## Effect of tool voltage on the deposition behavior



# Results and Discussion

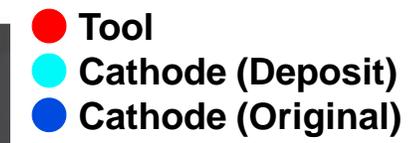
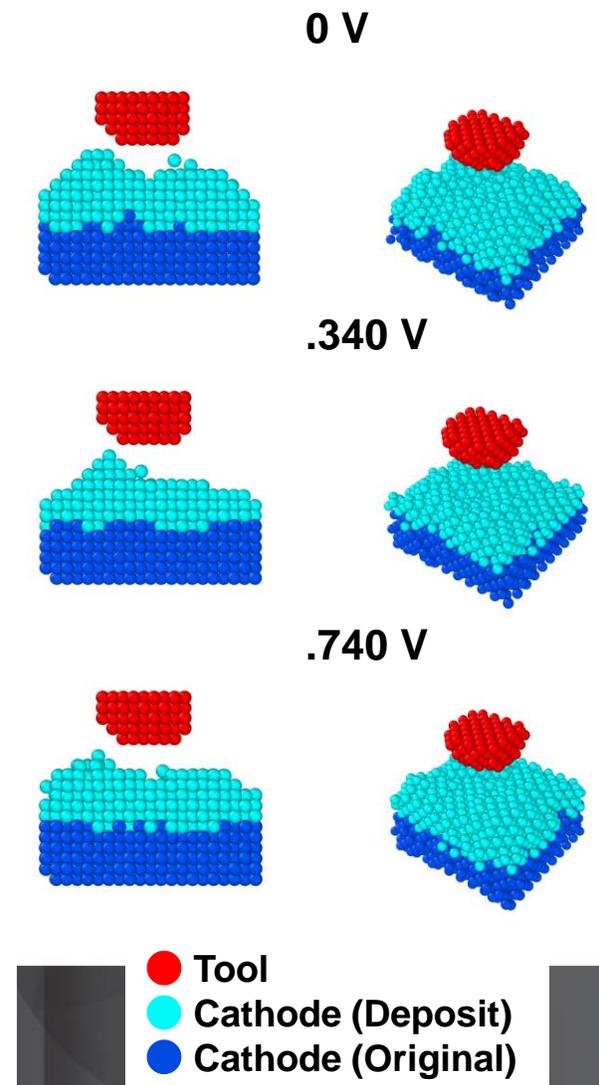
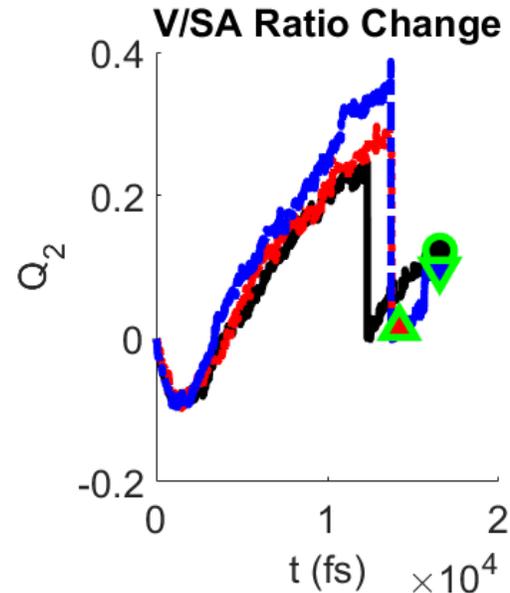
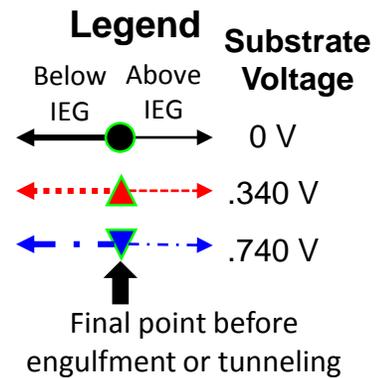
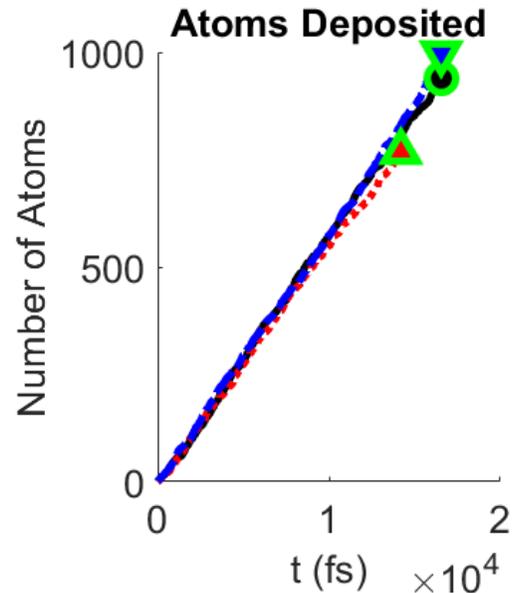
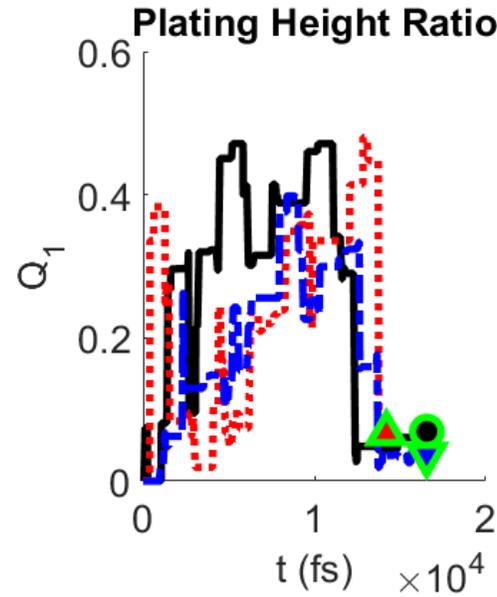
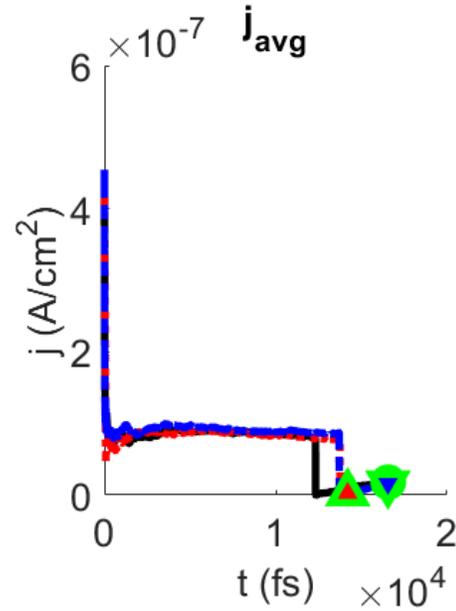
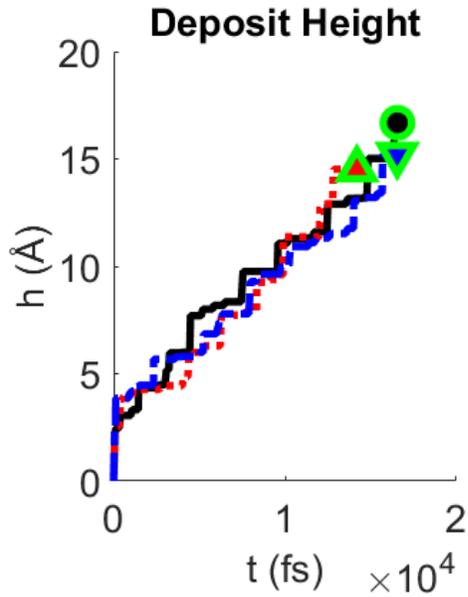


## Effect of tool voltage on the deposition behavior

- Effects of increasing the tool voltage
  - faster deposition and ion depletion from electrolyte, leading to sharp initial drop in current density
  - Improved localization of the overall deposit, but hollow region in center of deposit due to ion depletion immediately beneath the tool
- Effects of reducing the tool voltage
  - Opposite effect

# Results and Discussion

## Effect of substrate voltage on the deposition behavior



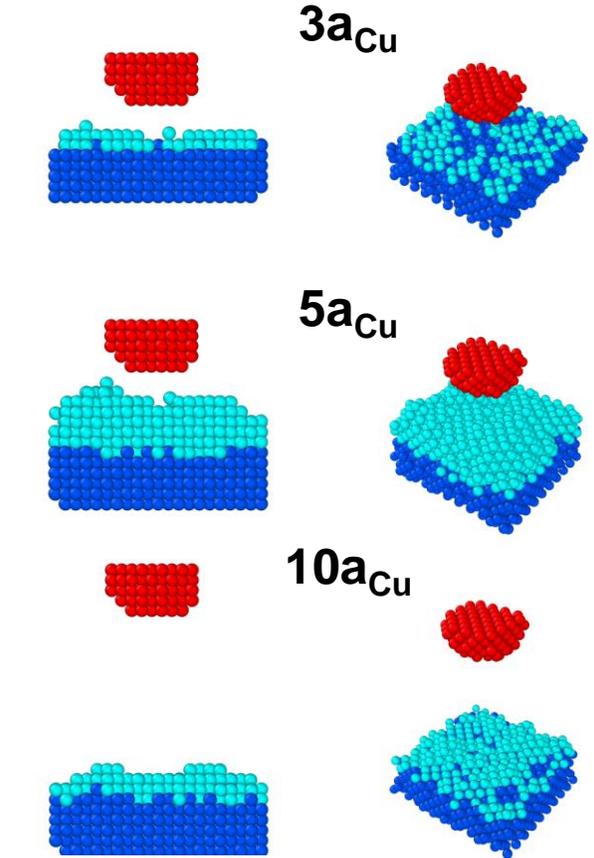
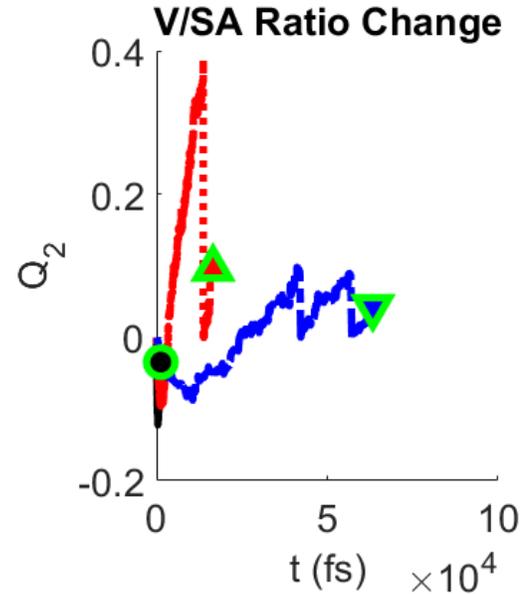
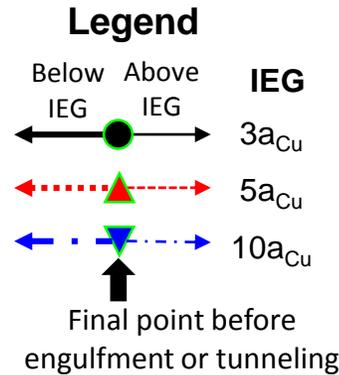
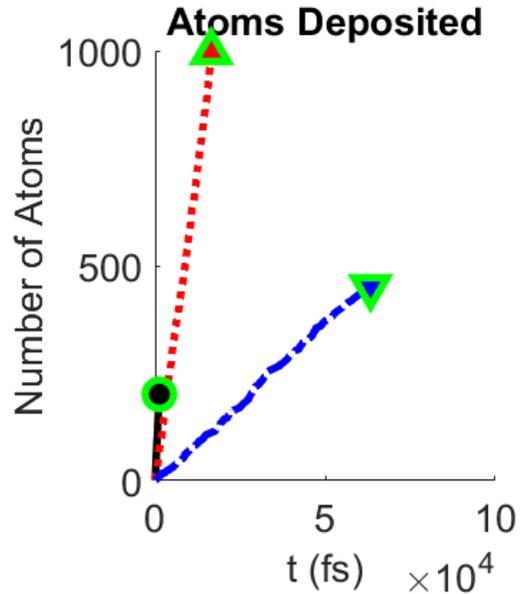
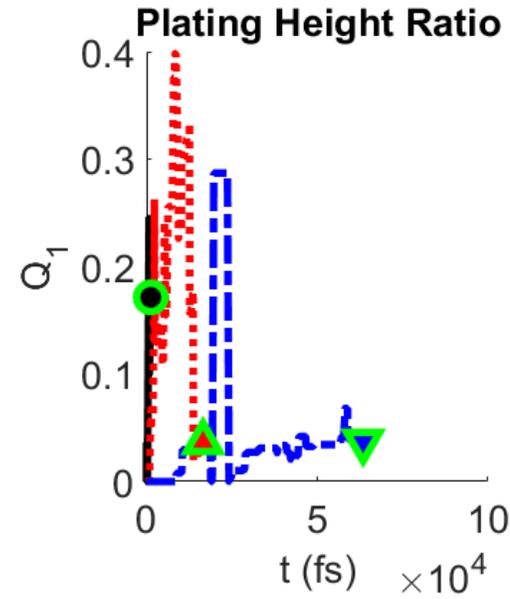
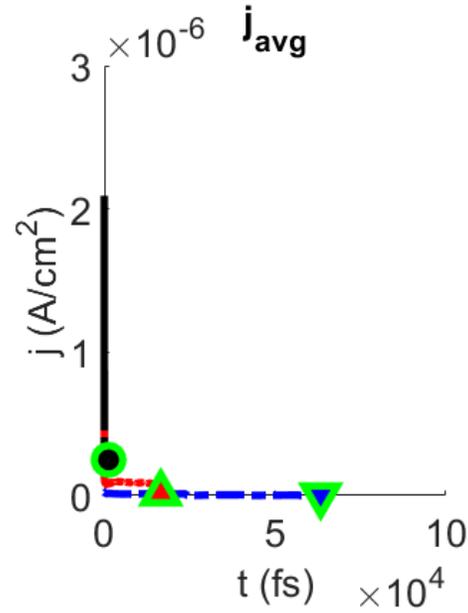
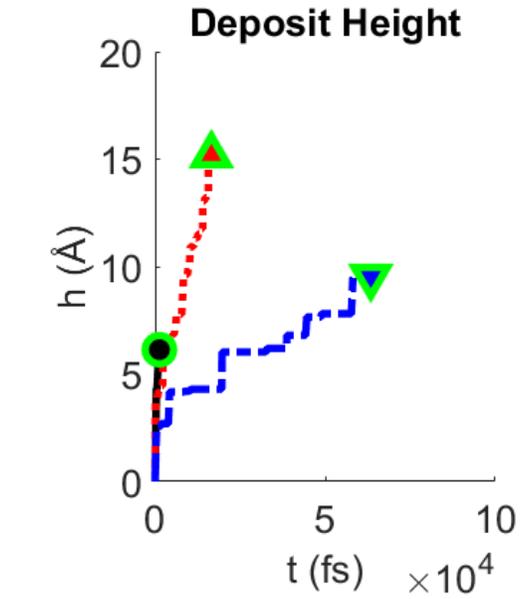
# Results and Discussion

## Effect of substrate voltage on the deposition behavior

- Effects of reducing the substrate voltage
  - Lowest value (corresponding to highest tool vs substrate difference) had similar effect as higher tool voltage - a faster ion depletion rate and hollow central region
- Effects of increasing the substrate voltage
  - Some subtle changes in the geometry and deposition rate, but not significant

# Results and Discussion

## Effect of interelectrode gap on the deposition behavior



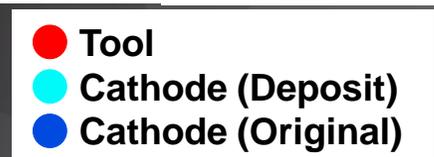
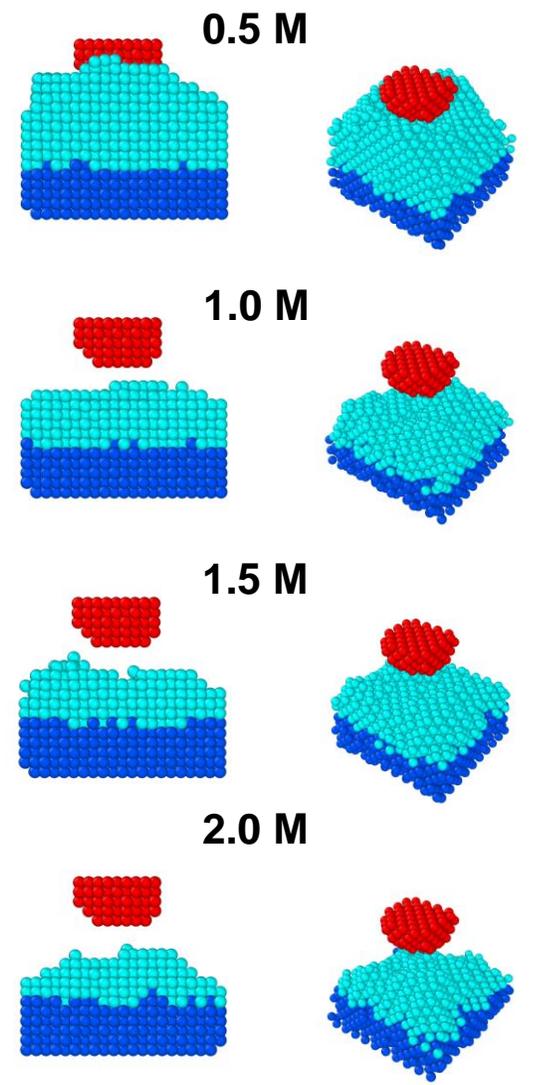
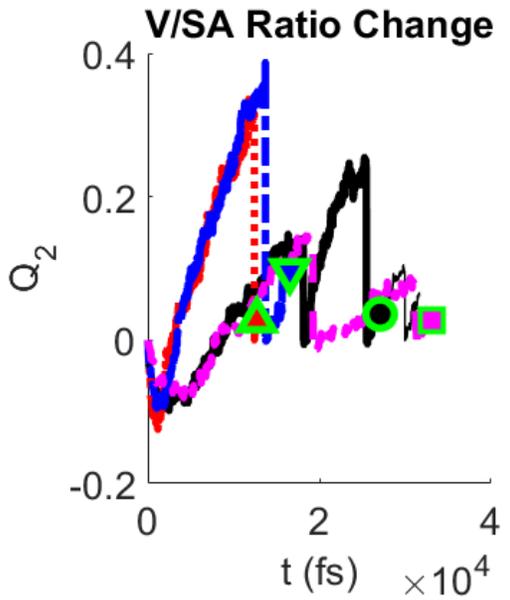
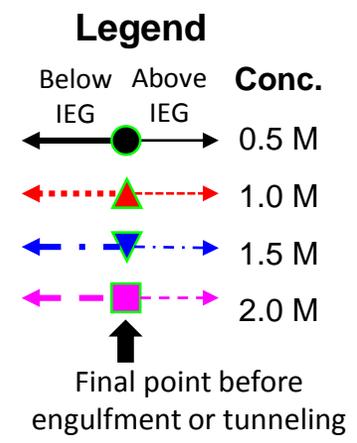
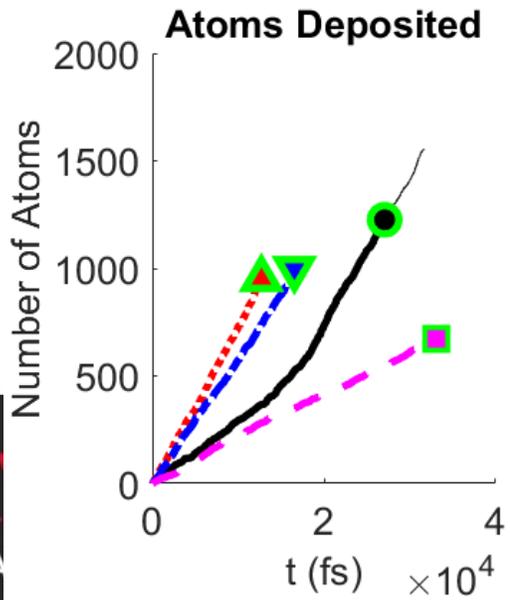
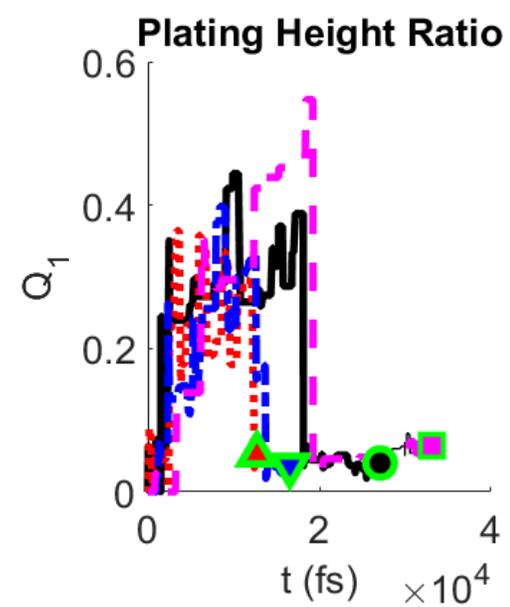
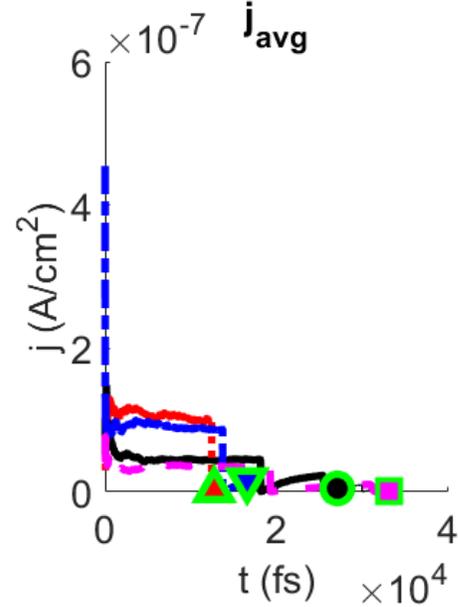
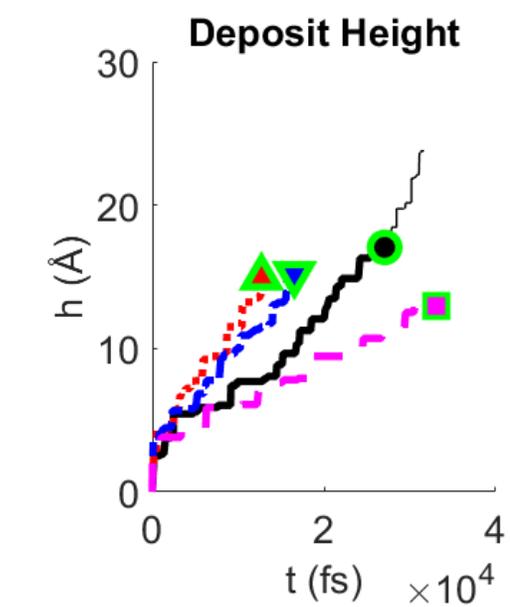
# Results and Discussion

## Effect of interelectrode gap on the deposition behavior

- Effects of increasing the interelectrode gap from the intermediate value
  - slower deposition
  - lower current density
  - Poor localization
- Effects of decreasing the interelectrode gap from the intermediate value
  - fastest deposition
  - rapid initial spike in current density
  - short-lived deposition resulting in a maximum height corresponding to two atomic layers
- Optimal interelectrode gap
  - The intermediate value of  $5a_{Cu}$  yielded an optimally-localized deposit

# Results and Discussion

## Effect of ion concentration on the deposition behavior



# Results and Discussion

## Effect of ion concentration on the deposition behavior

- Effects of increasing the ion concentration from the intermediate value
  - lower deposition speed and current density
  - highest quality of localization
- Effects of decreasing the ion concentration from the intermediate value
  - also lower deposition speed and current density
  - lowest quality of localization
- Intermediate ion concentrations
  - Highest deposition speeds and current densities

# Outline

- UC Micro and Nano Manufacturing Laboratory
- Electrochemical Additive Manufacturing (ECAM)
- Why molecular dynamics?
- System setup and method
- Results and discussion
- **Conclusions**
- Acknowledgments

# Conclusions

## Simulation method

- The localized electrochemical deposition process was modeled using a molecular dynamics simulation was performed
- Specifically, the migration and deposition of ions under the influence of charged, constant-potential electrodes was observed at varying input parameters (tool size, tool voltage, substrate voltage, interelectrode gap, and ion concentration)
- Deposition quality was evaluated quantitatively using two different quantitative approaches, as well as qualitative evaluation of the output geometry

# Conclusions

## Simulation output

- At a fixed interelectrode gap, the optimal radius for maximum deposition localization was found.
- Similarly, there was an optimal interelectrode gap at the radius studied for deposition quality,
- It was seen that varying the interelectrode gap and concentration allowed for inverse control over the deposition speed and quality – as deposition speed increased, quality decreased; and vice-versa.
- Variation of tool and substrate voltage gave a coupled change in deposition speed and quality, where both would simultaneously increase or decrease.
- Overall, with some exceptions, a higher tool-substrate voltage difference resulted in higher deposition speed and quality.
- Ion depletion behavior was seen in the runs with the highest voltage differentials and the lowest concentration, resulting in a hollow feature in the center of the deposit

# Outline



- UC Micro and Nano Manufacturing Laboratory
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# Acknowledgments



- This material is based upon work supported by the National Science Foundation under Grant No. CMMI-1454181 and CMMI-1955842.
- Any opinions, findings, and conclusions or recommendations expressed in this material are those of the author(s) and do not necessarily reflect the views of the National Science Foundation.
- High-performance computing resources were provided by the UC Mechanical and Materials Engineering Department.

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**Thank you for  
your time!  
Any questions?**